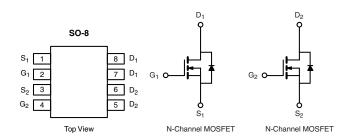
# **SQ4936EY**



**Vishay Siliconix** 

# Automotive Dual N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.036			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.053			
I <sub>D</sub> (A)	7			
Configuration	Dual			



#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- · Package with Low Thermal Resistance
- 100 %  $R_{\rm q}$  and UIS Tested
- AEC-Q101 Qualified<sup>c</sup>
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT HALOGEN

FREE

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4936EY-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unless	otherwise noted	ł)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	30		
Gate-Source Voltage		V <sub>GS</sub> ± 20		V	
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	7		
	T <sub>C</sub> = 125 °C	۱ <sub>D</sub>	4		
Continuous Source Current (Diode Conduction)		۱ <sub>S</sub>	3	A	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	28		
Single Pulse Avalanche Energy	L = 0.1 mH	I <sub>AS</sub>	13		
Single Pulse Avalanche Current	L = 0.1 MH	E <sub>AS</sub>	8	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P	3.3	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1.1		
Operating Junction and Storage Temperature	Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	110	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	45	0/10	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		30	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	2.5		
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A	-	0.027	0.036	Ω	
Durin Course On Otata Desistance	P	$V_{GS} = 10 V$	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C	-	-	0.056		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	-	0.067		
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 5 A	-	0.040	0.053		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 6 A	-	16	-	S	
Dynamic <sup>b</sup>							•	
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	664	830	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	143	180		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	59	75		
Total Gate Charge <sup>c</sup>	Qg		V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.8 A	-	13	20	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	2.3	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.1	-		
Gate Resistance	Rg	f = 1 MHz		0.7	-	2.3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:V_DD} \begin{array}{l} V_{DD} = 15 \; V, \; R_L = 15 \; \Omega \\ I_D \cong 5.8 \; A, \; V_GEN = 10 \; V, \; R_g = 1 \; \Omega \end{array}$		-	11	17	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	18	27		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	7	11		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	28	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.7 A, V <sub>GS</sub> = 0 V		-	0.8	1.2	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

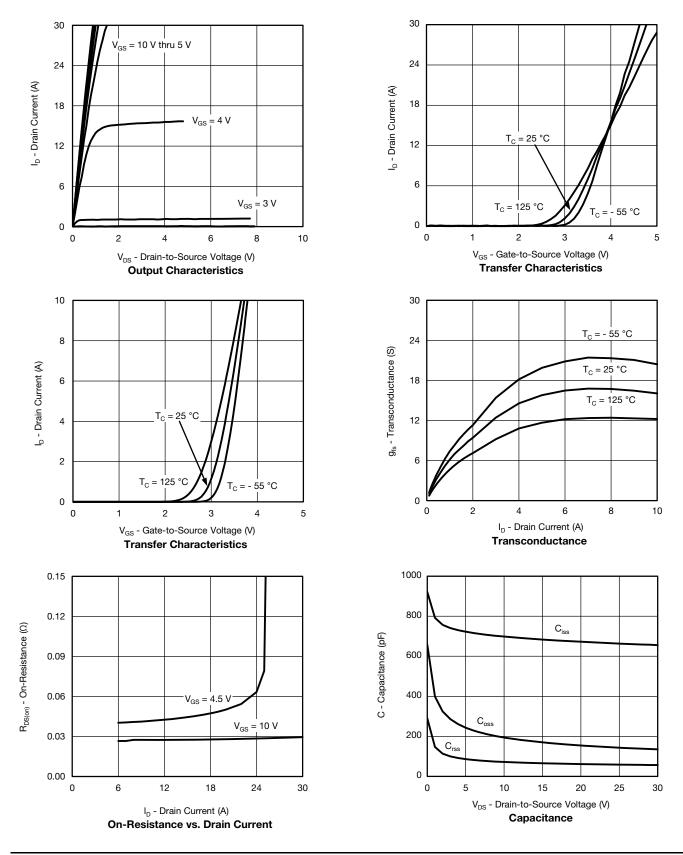
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S11-2113-Rev. B, 07-Nov-11

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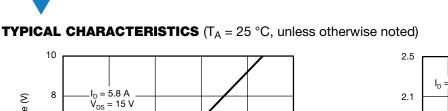
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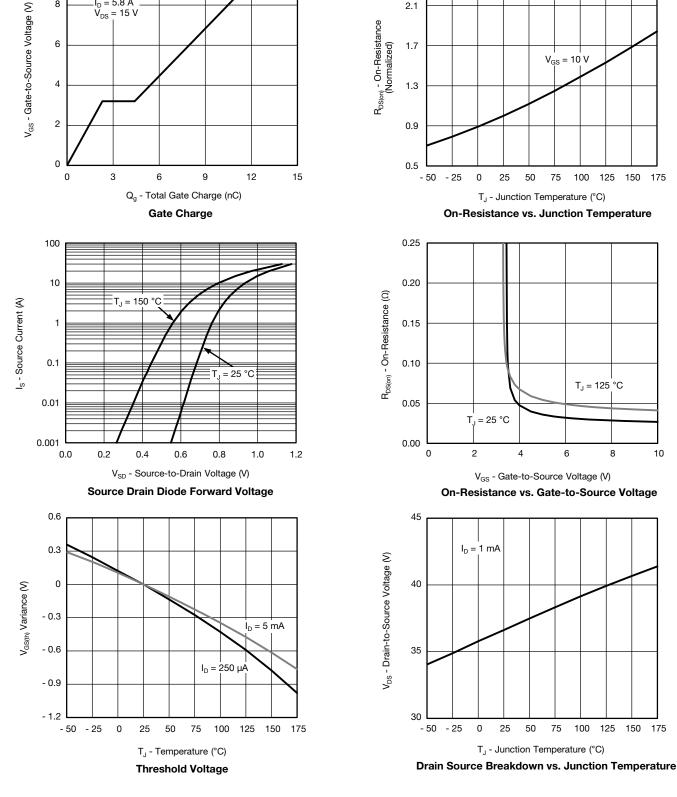
I<sub>D</sub> = 5.8 A 2.1



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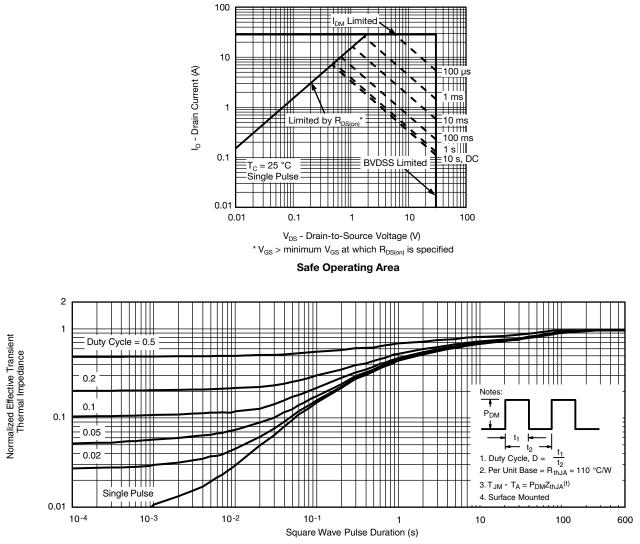
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

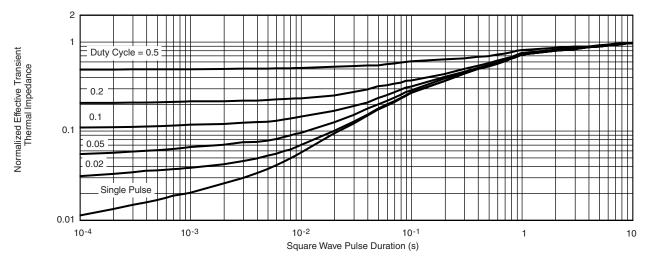


Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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